1. Decision taken by the JCTE Office on 09.05.2025 based on the complaints received from students of various Polytechnic Colleges in connection with the Diploma Examination April 2025 Question papers and recommendations of expert committee from different departments.

## OUT OF SYLLABUS/ DEFECTIVE QUESTIONS - Guidelines for valuation

R.21	Fundaments of Electrical and Electronics Engineering ( 2031 )	Part C Question No X	Within the syllabus
		Part C. Question No. III	If attended the first part, proportional mark shall be awarded to the second part too.
R.21	Fluid Mechanics & Heat Transfer (4111)	Part C. Question No. V(a)	If attended V (b), proportional mark shall be awarded to V (a).
		Part C. Question No. VII	This question is out of syllabus as recommended by the expert committee. Hence, following guidelines shall be used to calculate the mark of the students who had tried to attend the above specific questions.  (a) Calculate the percentage of marks obtained by the student considering the total marks excluding the marks of out of syllabus question.  (b) Then, the proportionate marks of out of syllabus question shall be calculated based on the above obtained percentage.  (c) Marks obtained in the above cases shall be added to get actual marks admissible to the student.
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V.V.RAY

JOINT CONTROLLER

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## **Scoring Indicators**

## COURSE NAME: FUNDAMENTALS OF ELECTRICAL & ELECTRONICS ENGINEERING

COURSE CODE: 2031

QID:2106220064

Q No	Scoring Indicators	Split score	Sub Total	Total Score
	PART A			9
I. 1	(a) Angular velocity - (B) Rad/S (b) Time period - (C) Sec (c) Frequency - (D) Hz (d) Impedance - (A) Ohm	1	1	
I.2	Volt	1	1	
I.3	$v = Vm \sin \omega t$	1	1	
I.4	Expanded form of MCB is Miniature Circuit Breaker	1	1	
I.5	Active Power = $\sqrt{3}$ VI cos $\phi$	1	1	
I.6	-\\\\-\\	1	1	
I.7	The transformer turns ratio is the number of turns of the primary winding divided by the number of turns of the secondary coil.	1	1	
1.8	Symbol of Zener diode	1	1	
1.9	Any two Clipping circuits, clamping circuits, rectifier, Voltage multiplier etc.	0.5x2	1	

	PART B			24
II. 1	Amplitude-1.5 Angular frequency-1.5	1.5x2	3	
	V= 25 Sin 628 t  Comparing with v = Vm sin ωt			
	Amplitude = 25 V			
	Angular frequency=628 rad/s			
II. 2	Definition-1x2 Unit-0.5x2	2+1	3	
(6)	Resistance is the property of a substance due to which it opposes the flow of current through it. Unit- Ohm			
(a)	Current is the rate of flow of electric charge.Unit-Ampere			3
II. 3	Effective resistance of parallel combination-1  Total effective resistance-2	1+2	3	
	Effective resistance of parallel combination=4  4=20hm Total effective resistance =3+2=50hm			
II. 4	Figure 1 mark Explanation 2 marks	1+2	3	
	Consider a rectangular coil of N turns placed in a uniform magnetic field as shown in the figure  Magnetic Field  The coil is rotating in the anticlockwise direction at an uniform angular velocity of ω rad/sec			

	When the coil is in the vertical	l position, the flux linking			
# EF	the coil is zero because the pla	ne of the coil is parallel to			
	the direction of the magnet	tic field. Hence at this			
	position, the emf induced in the	he coil is zero. When the			
	coil moves by some angle in th	ne anticlockwise direction,			
	there is a rate of change of	flux linking the coil and			
	hence an emf is induced in	the coil. When the coil		-	
	reaches the horizontal position	, the flux linking the coil			
9 9 9	is maximum, and hence th	e emf induced is also			
	maximum. When the coil	further moves in the			
	anticlockwise direction, the	emf induced in the coil			
	reduces. Next when the coi	il comes to the vertical			
	position, the emf induced bec	omes zero. After that the			
	same cycle repeats and the emf	is induced in the opposite			
	direction. When the coil c	completes one complete		3-0	
	revolution, one cycle of AC vol	tage is generated.			
II. 5			1		
11. 3	Any three differ	rence —3 x 1 marks each	mark each	3	
			Cacii	-	
					-
	Fuse	МСВ			ī
	Automatic protection	An either be automatic			
		or manually operated			
- +	Works on the thermal and	Works on the			
	electrical properties of the	switching principle			
	conducting materials	and electromagnetism			
	Fuse needs replacement	Can be used many			
	after a fault in circuit	numbers of times			
					,

II. 6 The first digit is 3, second digit is 3, third digit '3' multiplier in picofarads.  Capacitance = 33x10 <sup>3</sup> pF=33nF	is 3	3	
II. 7  Calculation 3 man	rks 1 mark each	3	
Red- 2			
Green- 5			
Brown- 1			
Gold -+/-5%			
Resistance = $25x \cdot 10^1 \pm 5 \%$ Ohm			
II. 8 Definition of Self inductance 1.5 ma	ırk		
Definition of Mutual inductance 1.5 mar	ks 1.5x2	3	
When a alternating current flows in a coil, the magnet field linking the coil also changes. Therefore, according to Faraday's law of electromagnetic induction, an EM known as self-induced EMF is induced. This property the coil to oppose the change in current.is call self-inductance.  Mathematically, self-induced EMF is given by, e=Ldi/dt where L is called as self inductance of the coil Mutual Inductance  Mutual Inductance  Mutual Inductance between the two coils is defined the property of the coil due to which it opposes the change of current in the other coil or the neighbouring coil. Mathematically, the mutually induced EMF is given by, em=M di <sub>1</sub> /dt where M is called mutual inductance	ng AF of ed as he ng		

II. 9	Definition of step up transformer - 1.5 marks  Definition of step down transformer - 1.5 marks	1.5 marks each	3	
	Step up transformer: A transformer that increases the voltage from primary to secondary (more secondary winding turns than primary winding turns) is called a step-up transformer. Transformation ratio >1  Step down transformer: A transformer that reduces the voltage from primary to secondary (more primary winding turns than secondary winding turns) is called a step-down transformer. Transformation ratio <1			f.
II. 10	INPUT OUTPUT  A B Y=A.B  0 0 0  0 1 0  1 0 0  1 1 1 1		3	£
	PART C			42
III	Circuit-1 Marks each Derivation-2 Marks each Final Equation-0.5 each	2+ 4+1	7	
	(a) Series: (b) Parallel: $V = V_1 + V_2$ $V = IR_1 + IR_2 = I(R_1 + R_2)$ $V = R_1 + R_2$ $R_1 = R_1 + R_2$ $R_2 = R_1 + R_2$ $R_2 = R_1 + R_2$			

IV	Faraday's Laws of Electromagnetic induction			
	First Law 3 marks	3+3+		
	Second Law 3 marks	3+3+ 1	7	:
	Equation 1 mark			5
	Faradays First Law:			
	Whenever magnetic flux linking with a conductor			
	changes an emf is induced in it.			
	Faradays Second Law:			
	The emf induced is directly proportional to rate of			
	change of flux linkage.			
	Flux linkage = flux * No of turns of the coil			
	$e \alpha \frac{d(N\dot{\phi})}{dt} Thus e = -N \frac{d\dot{\phi}}{dt}$			
				:
V	Energy consumption 4marks	4+3	7	
	Monthly electricity bill 3 marks	413	/	
	(a) Energy consumption in kWh in one day			
	$= \frac{40}{1000} \times 10 \times 5 + \frac{60}{1000} \times 5 \times 10 + \frac{1000}{1000} \times 1 \times 2 + \frac{250}{1000} \times 1 \times 20$			
	=12 kWh			
	(b) Monthly electricity bill for the month of December			
	$=12x \ 2x31 = Rs \ 744$			
VI	Power factor=2 marks	2+		
	Active power =2.5 marks	2.5+	7	:
	Reactive power=2.5 marks	2.5		
	Ф=30°			
	(a) Power factor = $\cos (30^{\circ}) = 0.866 \log$			
	(b) Active power = $VIcos\Phi$			
	$=100 \times 10 \times 0.866 = 866 \text{W}$			
	(c) Reactive power=VIsinΦ			
	A CONTRACTOR OF THE CONTRACTOR			1

VII	Definition-2 Marks each Expansion of ELCB-1 Marks	6+1	7	ß.
	<ul> <li>(a) Energy meter-The meter which is used for measuring the energy utilised by the electric load is known as the energy meter. The energy is the total power consumed and utilised by the load at a particular interval of time.</li> <li>(b) ELCB-Earth Leakage circuit Breaker. The main purpose of ELCB is to detect Earth leakages and prevent injury to human beings from electrical shocks and prevent electrical fires that are caused by short circuit</li> <li>(c) Main switch-The purpose of this switch is to control all the subcircuits provided in the building</li> </ul>			
VIII	Safety precautions while working with electricity Any 7 safety precautions $7 \times 1$ marks = $7$ marks	1 mark each	7	
	<ol> <li>Always use insulated tools while working.</li> <li>Never touch or try repairing any electrical equipment or circuits with wet hands.</li> <li>Never use equipment with frayed cords, damaged insulation or broken plugs.</li> <li>Before working on live mains, first switch off the supply of electricity to them</li> <li>If at all a person gets an electric shock, rescue him with the help of an insulator</li> <li>Never use metallic pencils or rulers, or wear rings or metal watch bands when working with electrical equipment</li> </ol>			· ·

IX	that wire a second of the seco	at no or other than the not sectrical end on other wear than the notion of the notion	tore high	clothing or ties	e into contact liquids near near electrical	3+4	7	
	Colour  Black Brown Red Orange Yellow Green Blue Violet Grey White Gold Silver None	1st Band 0 1 2 3 4 5 6 7 8	2 <sup>nd</sup> band 0 1 2 3 4 5 6 7 8	3rd band Multiplier  10°  10¹  10²  10³  10⁴  10⁵  10°  10°  10°  10°  10°  10°  10°	4 <sup>th</sup> band Tolerance ± 5 % ± 10 % ± 20 %			

	Color coding is used to identify the value of the resistor. The first two color bands represent the first two significant digits of the resistor value. The color of the third band represents a multiplier of $10^N$ , where N is the value represented by the color. The fourth band is always gold or silver, which indicates a tolerance of $\pm 5\%$ or $\pm 10\%$ .  First Second * $10^N$ Multiplier Second Band Multiplier Tolerance			
X	Circuit-2 Marks Derivation-4Marks Equation-1 Marks	1+6	7	
	Here Q is same $Q = C_{eff}V$ $V = V_1 + V_2 = \frac{Q}{C} + \frac{Q}{C} = \frac{2Q}{C}$ $Q = \frac{CV}{2}$ Comparing, $C_{eff} = \frac{c}{2}$			

XI	Full Wave Bridge Rectifier circuit			
	Circuit diagram 2 marks	2+		
	Waveforms 2 marks	3+2	7	
	Operation 3 marks			
	Vin			
	During the positive half cycle of the secondary voltage,			
	the end A becomes positive, and end B becomes			
	negative. The diodes D <sub>1</sub> and D <sub>3</sub> are forward biased and			
	the diodes D <sub>2</sub> and D <sub>4</sub> are reverse biased. Therefore,			
	diodes D <sub>1</sub> and D <sub>3</sub> conduct and diodes D <sub>2</sub> and D <sub>4</sub> do not			*)
	conduct. The current flows through diode D <sub>1</sub> , load			
	resistor R <sub>L</sub> (from M to L), diode D <sub>3</sub> and the transformer			
	secondary.			
	During the negative half cycle, the end A becomes			
	negative and end B positive. The diodes D <sub>2</sub> and D <sub>4</sub> are			
	forward biased and the diodes D <sub>1</sub> and D <sub>3</sub> are reverse			
	biased. Therefore, diodes D <sub>2</sub> and D <sub>4</sub> conduct while			
	diodes D <sub>1</sub> and D <sub>3</sub> do not. Thus, current thus flows			
	through the diode D <sub>2</sub> , load resistor R <sub>L</sub> (from M to L),			:
	diode D <sub>4</sub> and the transformer secondary. The current			
	flows through the load resistor RL in the same direction			
	(M to L) during both the half cycles. Hence, a DC output			
	voltage V <sub>out</sub> is obtained across the load resistor.			
	I and the second	I	1	

Figures 3 marks		7	
	4+3	,	
Operation:			
A Zener Diode, also known as a breakdown diode, is a			
heavily doped semiconductor device that is designed to			
operate in the reverse direction. When the voltage across			
the terminals of a Zener diode is reversed and the			
potential reaches the Zener Voltage (knee voltage), the			
junction breaks down and the current flows in the			
reverse direction. This effect is known as the Zener			
Effect			
A Zener diode operates just like a normal diode when it			
is forward-biased. However, when connected in reverse			
biased mode, a small leakage current flows through the			
diode. As the reverse voltage increases to the			
predetermined breakdown voltage (Vz), current starts			
flowing through the diode. The current increases to a			
maximum, which is determined by the series resistor,			
after which it stabilizes and remains constant over a wide			
range of applied voltage.			
There are two types of breakdowns for a Zener Diode:			
Avalanche Breakdown			
Zener Breakdown			
Forward Characteristics of Zener Diode			
It is almost identical to the forward characteristics of any			
other P-N junction diode.			
Reverse Characteristics of Zener Diode			
When a reverse voltage is applied to a Zener voltage,			
initially a small reverse saturation current Io flows across	-		
the diode. This current is due to thermally generated			
minority carriers. As the reverse voltage is increased, at			
a certain value of reverse voltage, the reverse current			
	A Zener Diode, also known as a breakdown diode, is a heavily doped semiconductor device that is designed to operate in the reverse direction. When the voltage across the terminals of a Zener diode is reversed and the potential reaches the Zener Voltage (knee voltage), the junction breaks down and the current flows in the reverse direction. This effect is known as the Zener Effect  A Zener diode operates just like a normal diode when it is forward-biased. However, when connected in reverse biased mode, a small leakage current flows through the diode. As the reverse voltage increases to the predetermined breakdown voltage (Vz), current starts flowing through the diode. The current increases to a maximum, which is determined by the series resistor, after which it stabilizes and remains constant over a wide range of applied voltage.  There are two types of breakdowns for a Zener Diode:  • Avalanche Breakdown  • Zener Breakdown  Forward Characteristics of Zener Diode  It is almost identical to the forward characteristics of any other P-N junction diode.  Reverse Characteristics of Zener Diode  When a reverse voltage is applied to a Zener voltage, initially a small reverse saturation current Io flows across the diode. This current is due to thermally generated minority carriers. As the reverse voltage is increased, at	A Zener Diode, also known as a breakdown diode, is a heavily doped semiconductor device that is designed to operate in the reverse direction. When the voltage across the terminals of a Zener diode is reversed and the potential reaches the Zener Voltage (knee voltage), the junction breaks down and the current flows in the reverse direction. This effect is known as the Zener Effect  A Zener diode operates just like a normal diode when it is forward-biased. However, when connected in reverse biased mode, a small leakage current flows through the diode. As the reverse voltage increases to the predetermined breakdown voltage (Vz), current starts flowing through the diode. The current increases to a maximum, which is determined by the series resistor, after which it stabilizes and remains constant over a wide range of applied voltage.  There are two types of breakdowns for a Zener Diode:  • Avalanche Breakdown  Forward Characteristics of Zener Diode  It is almost identical to the forward characteristics of any other P-N junction diode.  Reverse Characteristics of Zener Diode  When a reverse voltage is applied to a Zener voltage, initially a small reverse saturation current Io flows across the diode. This current is due to thermally generated minority carriers. As the reverse voltage is increased, at	A Zener Diode, also known as a breakdown diode, is a heavily doped semiconductor device that is designed to operate in the reverse direction. When the voltage across the terminals of a Zener diode is reversed and the potential reaches the Zener Voltage (knee voltage), the junction breaks down and the current flows in the reverse direction. This effect is known as the Zener Effect  A Zener diode operates just like a normal diode when it is forward-biased. However, when connected in reverse biased mode, a small leakage current flows through the diode. As the reverse voltage increases to the predetermined breakdown voltage (Vz), current starts flowing through the diode. The current increases to a maximum, which is determined by the series resistor, after which it stabilizes and remains constant over a wide range of applied voltage.  There are two types of breakdowns for a Zener Diode:  Avalanche Breakdown  Zener Breakdown  Porward Characteristics of Zener Diode  It is almost identical to the forward characteristics of any other P-N junction diode.  Reverse Characteristics of Zener Diode  When a reverse voltage is applied to a Zener voltage, initially a small reverse saturation current Io flows across the diode. This current is due to thermally generated minority carriers. As the reverse voltage is increased, at

	increases drastically and sharply. This voltage is called			
	breakdown voltage or Zener voltage and it is denoted by			*
	Vz.			
	Current			
	Breakdown Voltage, Vz  Leakage Current  Avalanche Current  Reverse Voltage  Threshold Voltage (for silicon diodes, Vth≈0.7V)  Reverse Voltage  Stables voltage of the page of			Ť
XIII	Sketches showing proper biasing 3 marks  Explanation 4 marks	3+4	7	
	Transistor can be used to increase the strength of the weak input signals without distorting the signal and hence used as amplifiers. For a transistor to work as an amplifier ,it should be operated in the active region. Common Emitter configuration is commonly used for amplification, due to high current, voltage and power gain. The circuit diagram is shown below:  The weak input signal is applied between emitter and base junction while the output is taken across the load resistor $R_{\mathcal{C}}$ connected in series with collector supply voltage $V_{\mathcal{CC}}$ . For faithful amplification input circuits should be forward biased and have low resistance. Small			*
	should be forward biased and have low resistance. Small			

	change in input voltage causes relatively large change in collector current ( $I_C = \beta I_B$ ; $\beta$ being large). The collector			
	current flowing through a high load resistance $R_C$		71	
	develops a large voltage across it. Thus it functions as an			
	amplifier.		7 .	
	Transistor as an Amplifier in Common Emitter $i_C$ $i_C$ $i_C$ $i_B$ SIGNAL			
	$I_{BB} \qquad I_{CC} \qquad I_{CC} \qquad I_{C} \qquad I$			
XIV	Symbol of gate – 1.5 mark each (3 marks)  Truth Table – 2 marks each (4 marks)	3+4	7	
	NAND gate: XOR gate:			
	NAND gate Exclusive-OR gate			
	Input <sub>A</sub> Output Input <sub>B</sub> Output	,		
	A       B       Output         0       0       1         0       1       1         1       0       1         1       1       0         1       1       0         1       1       0			ž.